

GaAs Schottky Diode

Extremely Fast Recovery for RF & MHz Switching Applications

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Description

This new line of High Speed GaAs Schottky Diodes provide extremely fast recovery times, outperforming both Ultrafast and Silicon Carbide technologies. The recovery times and low junction capacitances combined with their inherently low forward voltages make this new product family ideal for High Frequency Converters, Resonant Converters and Switch Mode Power Supplies operating from the KHz-MHz range.

The GaAs devices are packaged in the low inductance, low profile, electrically isolated, surface mount DE-150 package. The matched thermal coefficient of expansion between the aluminum nitride substrate and the GaAs Diode result in improved reliability and power cycling performance.

The GaAs Schottky products have an added advantage when used in conjunction with the DE Series Switch Mode & RF Mosfets. Both products utilize the same package profiles resulting in a convenient single plane to heat sink.

Each device contains three diodes, with three different configuration options; Triple Independent, Triple Common Cathode, and Triple Common Anode.

Advantages

- Extremely Fast Reverse Recovery Times, Typically <15nS
- · Much lower forward Voltage than Silicon Carbide
- · Isolated, low inductance, surface mount, high power package

SUMMARY TABLE - GaAs SCHOTTKY

Part Type	V _{RRM}	I _{D(25)}	C _{JUNCTION}	V _{F(IF=2A)}	P _{TOT(25)}	R _{THJC}
*GS150T_25104	250 V	4 A	9pF	1.5V	9 W	16.3 C/W
*GS150T_25110	250 V	10 A	18pF	1.5V	15 W	9.6 C/W
*GS150T_25120	250 V	20 A	36pF	1.5V	20 W	7.2 C/W
*GS150T_25150	250 V	50 A	TBD	TBD	TBD	TBD

*Three configuration options available: TI - Triple Independent, TC - Triple Common Cathode, TA - Triple Common Anode Example: GS150Tl25104 - The Triple Independent version.

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